F. Silicon and Group-IV Devices and Integration Technology 분과

2017년 2월 15일 (수), 12:40-14:25 Room E (루비, 2층)

[WE3-F] Advanced CMOS Integrated Circuits

좌장: 조성재(가천대학교), 조일환(명지대학교)

WE3-F-1 12:40-12:55	Analysis on Switching Characteristic of Tunnel Field-Effect Transistor NAND and NOR Circuit Dae Woong Kwon, Junil Lee, Euyhwan Park, Sihyun Kim, Ryoongbin Lee, and Byung-Gook Park Department of Electrical and Computer Engineering, Seoul National University
WE3-F-2 12:55-13:10	Learning with Neuron-Synapse Connection in Neuromorphic System Jeong-Jun Lee, Jungjin Park, Hyungjin Kim, and Byung-Gook Park Department of Electrical Engineering, Seoul National University
WE3-F-3 13:10-13:25	Synaptic Devices based on Reconfigurable Gated Schottky Diodes for Highly-Linear Potentiation Suhwan Lim, Jong-Ho Bae, Jun-Mo Park, Jai-Ho Eum, Won-Mook Kang, Chul-Heung Kim, Myoung-Sun Lee, Sung Yun Woo, Byung-Gook Park, and Jong-Ho Lee Department of ECE and ISRC, Seoul National University
WE3-F-4 13:25-13:40	Reconfigurable Device with Programmable Bottom Gate Array Jong-Ho Bae, Jun-Mo Park, Jai-Ho Eum, Won-Mook Kang, Jaeha Kim, Byung-Gook Park, and Jong-Ho Lee Department of Electrical and Computer Engineering, Seoul National University and Inter-university Semiconductor Research Center, Seoul National University
WE3-F-5 13:40-13:55	Enhanced Signal Acquisition Design for Complex Electrophysiological Interface Woojin Ahn, Cheonju Ko, Byungjik Kim, Suji Lee, Jiyoon Kim, and Seunghoon Lee <i>Ybrain Research Institute</i>
WE3-F-6 13:55-14:10	Integrate-and-Fire (I&F) Neuron Circuit Using Positive Feedback Field Effect Transistor (FBFET) Min-Woo Kwon, Sungmin Hwang, Myung-Hyun Baek, Jungjin Park, and Byung-Gook Park Department of Electrical and Computer Engineering, Seoul National University
WE3-F-7 14:10-14:25	Light Emission from a P-Diffused Inverted-rib Germanium Laser Structure Chan-Hyuck Park ¹ , Motoki Yako ² , Yasuhiko Ishikawa ² , Kazumi Wada ² , and Donghwan Ahn ¹ ¹ School of Materials Science and Engineering, Kookmin University, ² Department of Materials Engineering, University of Tokyo